# **CPH3456**

# Power MOSFET 20V, 71m $\Omega$ , 3.5A, Single N-Channel



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#### **Features**

- ON-Resistance  $R_{DS}(on)1=54m\Omega$  (typ)
- 1.8V Drive
- Pb-Free, Halogen Free and RoHS Compliance

	VDSS	R <sub>DS</sub> (on) Max	ID Max	
		71 mΩ@4.5V		
	20V	103 mΩ@2.5V	3.5A	
		156 mΩ@1.8V		

#### **Specifications**

#### **Absolute Maximum Ratings** at Ta = 25°C

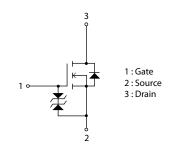
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V <sub>DSS</sub>	20	V
Gate to Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (DC)	ID	3.5	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	14	Α
Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm)	PD	1.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

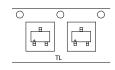
#### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm²×0.8mm)	R <sub>θJA</sub>	125	°C/W

## Electrical Connection N-Channel



Packing Type:TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

<sup>\*</sup> Machine Model

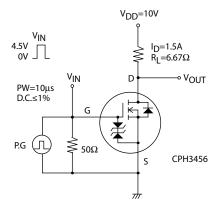
#### **CPH3456**

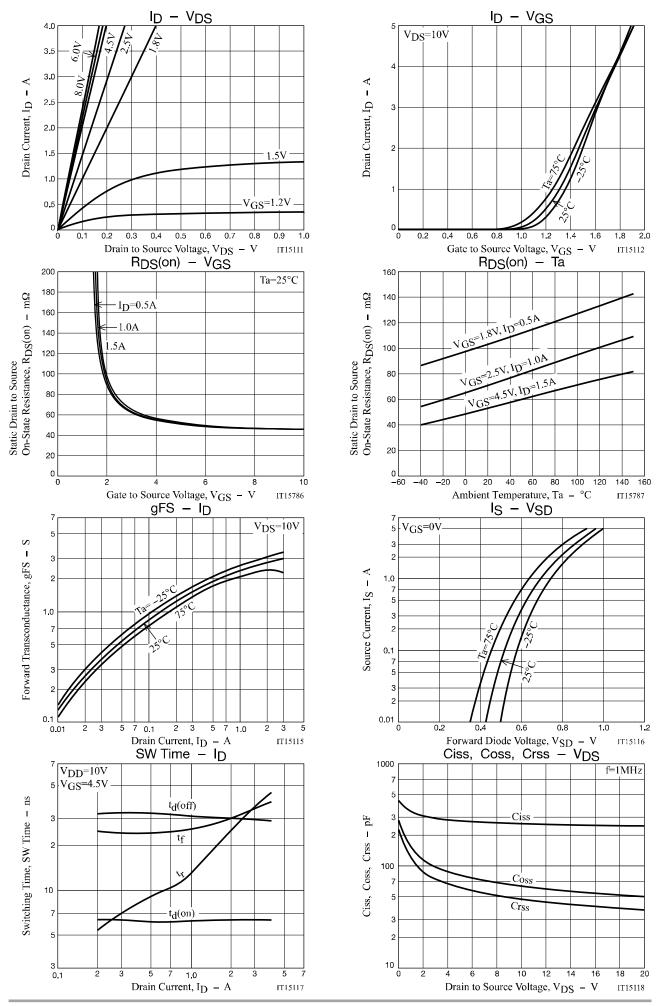
#### **Electrical Characteristics** at $Ta = 25^{\circ}C$

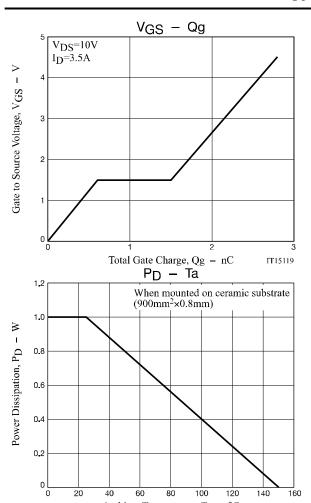
Parameter	Symbol	Conditions	Value			11-4
Parameter			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			٧
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A		2.8		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =1.5A, V <sub>GS</sub> =4.5V		54	71	mΩ
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		73	103	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V		104	156	mΩ
Input Capacitance	Ciss			260		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		65		pF
Reverse Transfer Capacitance	Crss	1		50		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			6.2		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		19		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			30		ns
Fall Time	t <sub>f</sub>	7		28		ns
Total Gate Charge	Qg			2.8		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A		0.6		nC
Gate to Drain "Miller" Charge	Qgd	7		0.9		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =3.5A, V <sub>GS</sub> =0V		0.85	1.2	V

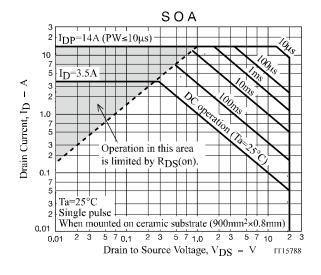
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

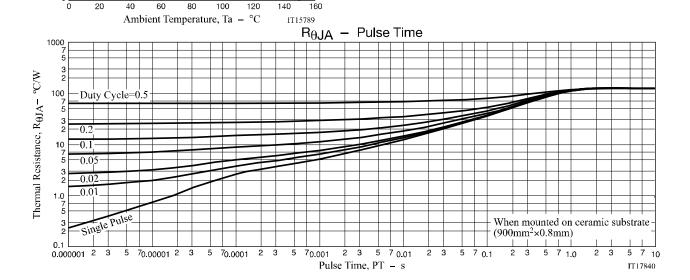
### **Switching Time Test Circuit**











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#### **Package Dimensions**

CPH3456-TL-H/ CPH3456-TL-W

#### CPH3

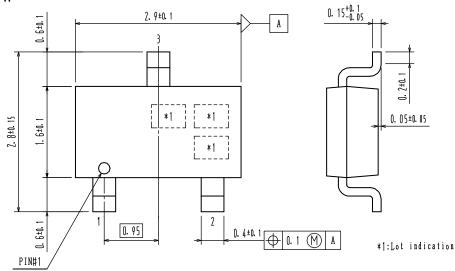
CASE 318BA ISSUE O

Unit: mm

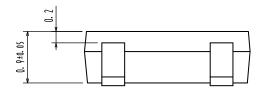
1: Gate

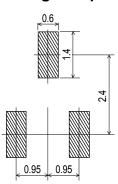
2 : Source

3: Drain



# Recommended Soldering Footprint





#### ORDERING INFORMATION

Device	Package	Shipping	Note	
CPH3456-TL-H	CPH3, SC-59	3,000	Pb-Free and	
CPH3456-TL-W	SOT-23, TO-236	pcs. / reel	Halogen Free	

Note on usage : Since the CPH3456 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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